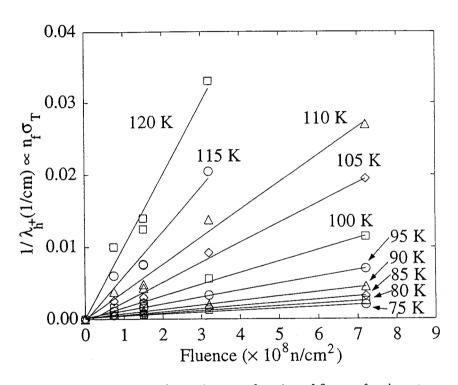


# Radiation Damage in Ge

- Radiation damage produces predominantly hole traps (no electron traps?).
- Amount of traps depends on type of particle, particle fluence, crystal temperature, temperature history, crystal type (n or p)....
- Trapping length depends on amount of traps and electric field (|E|).
- Spectral response and pulse shape depends on electric field (E), trapping length and electrode geometry (weighting potential).



### Radiation Damage in Ge

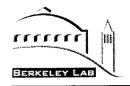


13  $\times 10^{-11}$  (cm/n)  $\sigma_{\mathrm{T}}$ 8 689-4.9 Fluence  $(n/cm^2)$ 691-15.7  $1/\lambda_{h^+}(1/cm)$ (n-type) (n-type) p-type planars 90 100 70 80 110 120 T(K)

Figure 3.8: The amount of trapping as a function of fluence for the p-type planar detectors. The lines are fit to the data with a linear regression analysis.

Figure 3.9: Hole-trap cross section as a function of temperature, fluence, typeness of detector, and the net impurity concentration of n-type detectors.

#### E. L. Hull, PhD Thesis, Indiana University, May 1998



## Radiation Damage in Ge

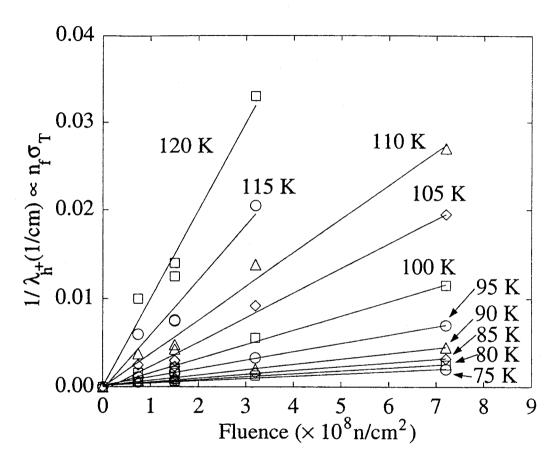


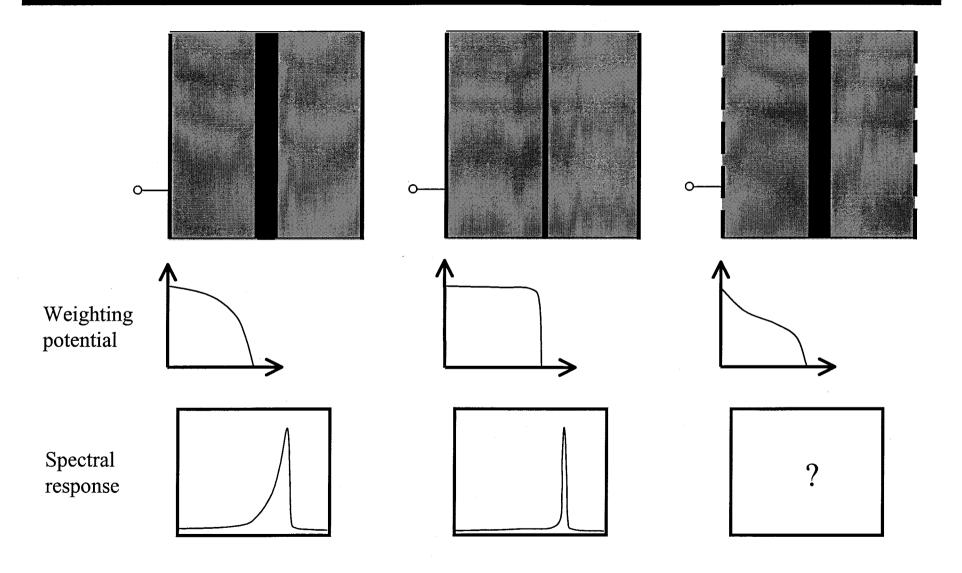
Figure 3.8: The amount of trapping as a function of fluence for the p-type planar detectors. The lines are fit to the data with a linear regression analysis.

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# Effects of Electrode Geometry



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